

FIG. 1

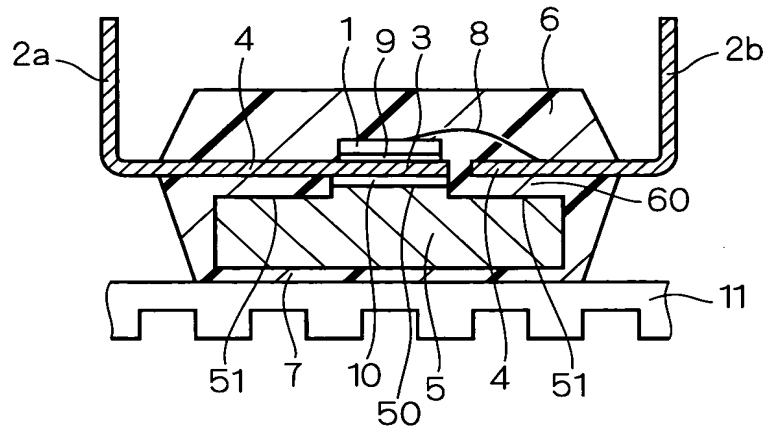


FIG. 2 A

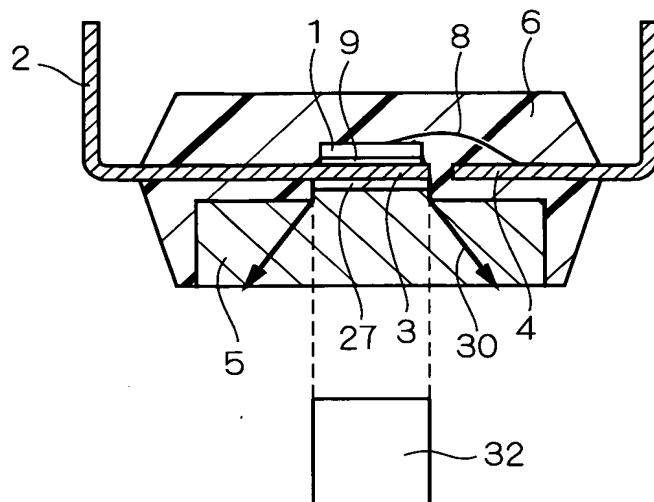
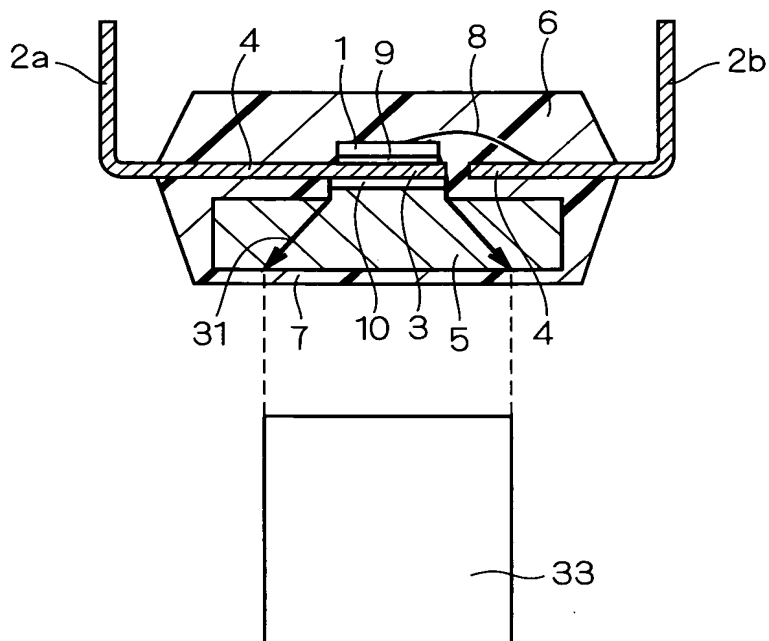


FIG. 2 B



F I G . 3

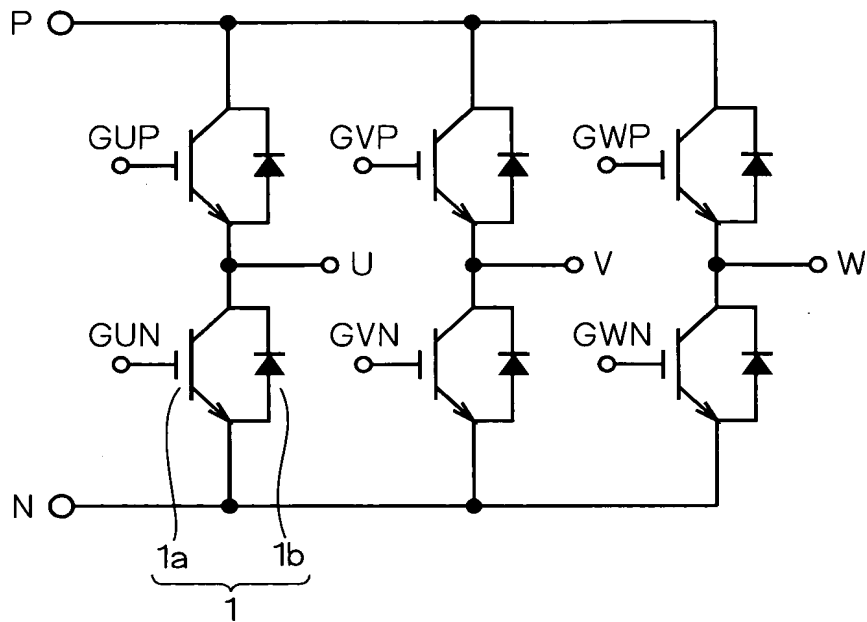




FIG. 4.

A cross-sectional view of a semiconductor device. It features a substrate 2 with a base layer 3. On the substrate, there are two semiconductor elements 1, each consisting of a first semiconductor layer 1a and a second semiconductor layer 1b. The elements are separated by a trench 4. A gate structure 5 is formed over the elements, with a gate insulating layer 6 and a gate electrode 8. The gate electrode is connected to a gate line 9. The device is surrounded by a protective layer 10, and a passivation layer 17 is formed over the gate structure. A contact layer 18 is formed over the gate electrode.

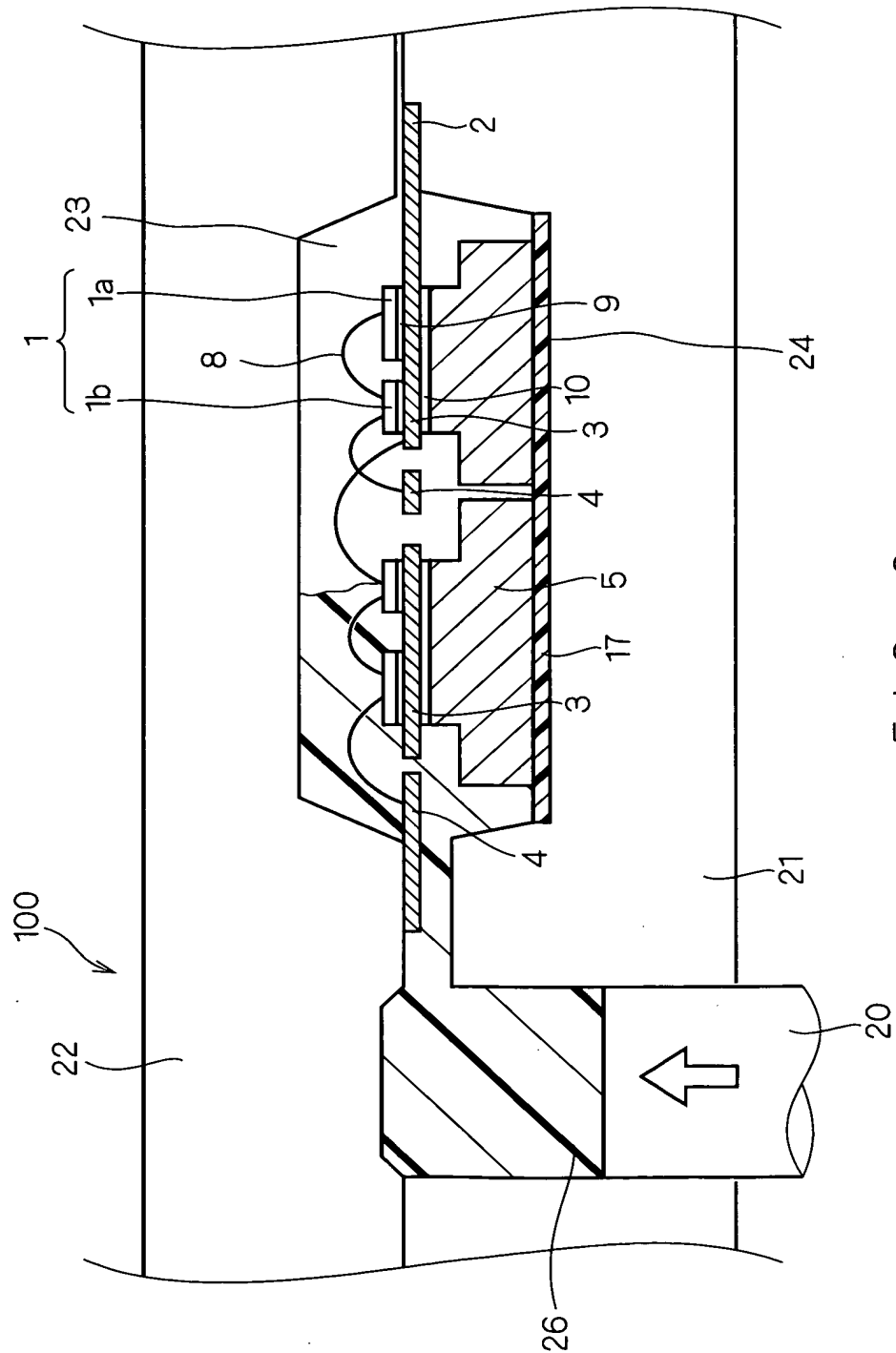


FIG. 6

FIG. 7

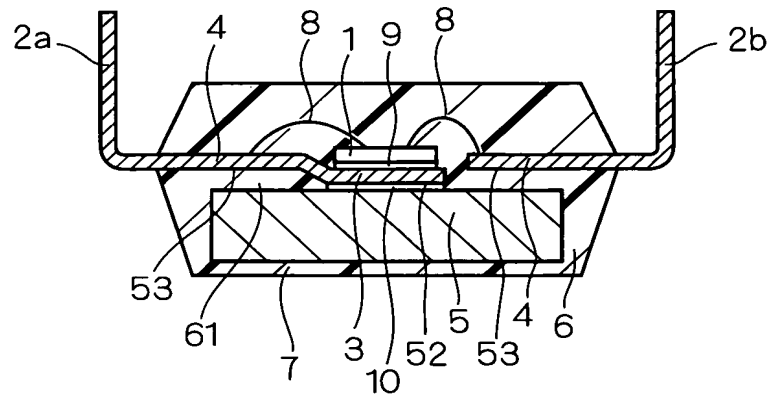


FIG. 8

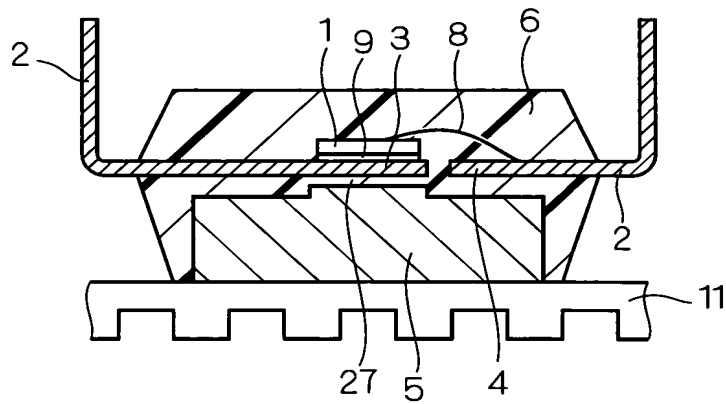


FIG. 9

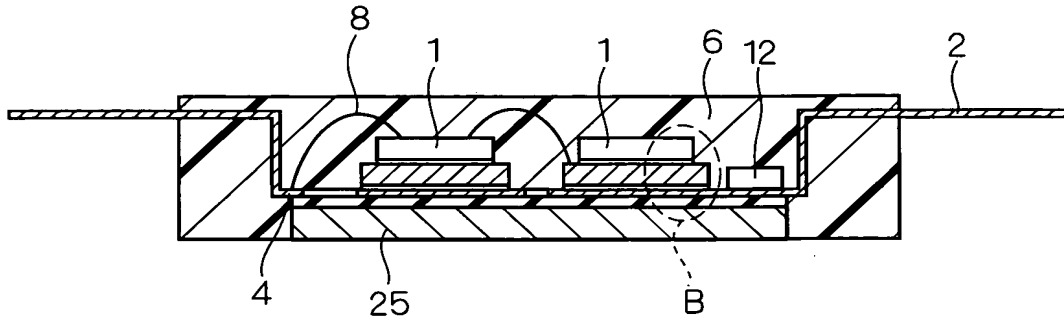


FIG. 10

